

SuperMOS – PDFN3*3-8L 100V BV_{DSS}, 82mΩ R_{DS(ON)}, N-channel MOSFET

1. Description

The ESN4486 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN4486 is Pb-free.

2. Features

- 100V, R_{DS(ON)}=82mΩ(Tpy.) @V_{GS}=10V
R_{DS(ON)}=90mΩ(Tpy.) @V_{GS}=4.5V
 - Use trench MOSFET technology
 - High density cell design for low R_{DS(on)}
- Material: Halogen free
 - Reliable and rugged
 - Avalanche Rated
 - Low leakage current

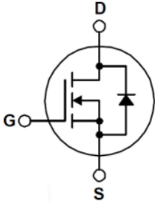
3. Applications

- PWM applications
 - Load switch
 - Power management in portable/desktop PCs
 - DC/DC conversion
- 100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESN4486	PDFN3*3-8L	ESN4486/lot	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate	Note d 	
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^{\circ}\text{C}$	I_D	10	A
	$T_C=75^{\circ}\text{C}$		8	
Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	P_D	20	W
	$T_C=75^{\circ}\text{C}$		12	
Pulsed Drain Current ^a		I_{DM}	40	A
Avalanche Current, Single Pulsed ^b		I_{AS}	12.5	A
Avalanche Energy, Single Pulsed ^b		E_{AS}	23.4	mJ
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Lead Temperature		T_L	260	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JA}$		110	$^{\circ}\text{C/W}$
Junction-to-Case Thermal Resistance ^c	Steady State	$R_{\theta JC}$		6.3	

Note:

a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

b: EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=50\text{V}$, $V_G=10\text{V}$, $L=0.3\text{mH}$, $R_g=25\Omega$

c: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

d: This diagram is only an electrical schematic, and the actual pin size is based on POD.

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.0	1.8	3.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =10V, I _D =4A		82	122	mΩ
		V _{GS} =4.5V, I _D =3A		90	142	
Forward Trans conductance	g _{FS}	V _{DS} =5.0V, I _D =4A			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=1MHz, V _{DS} =25V		815		pF
Output Capacitance	C _{OSS}			50		
Reverse Transfer Capacitance	C _{RSS}			35		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =4.5V, V _{DS} =50V, I _D =2A		12		nC
Gate-to-Source Charge	Q _{GS}			2.6		
Gate-to-Drain Charge	Q _{GD}			2.8		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =50V, R _L =1Ω, R _G =3Ω		7		ns
Rise Time	t _r			5		
Turn-Off Delay Time	t _{d(OFF)}			18		
Fall Time	t _f			8		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A		0.7	1.2	V

7. Typical Characteristic

Figure1: Output Characteristics

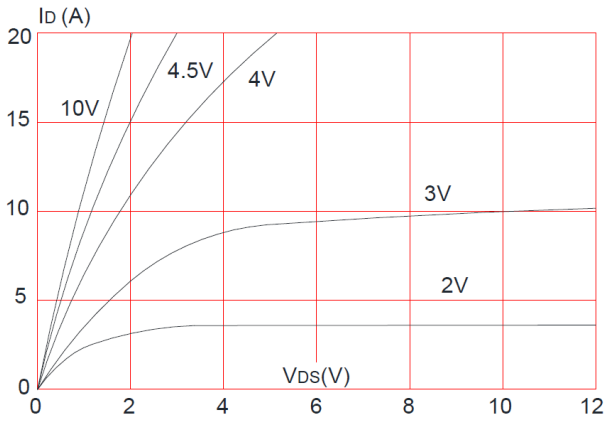


Figure 2: Typical Transfer Characteristics

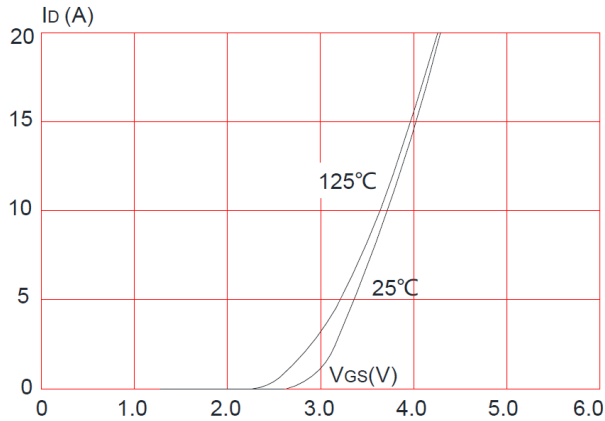


Figure 3: On-resistance vs. Drain Current

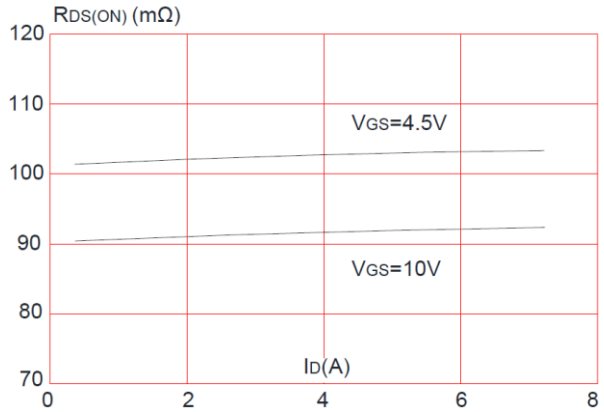


Figure 4: Body Diode Characteristics

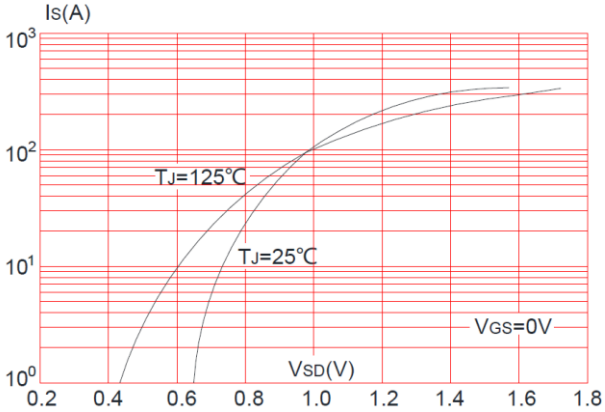


Figure 5: Capacitance Characteristics

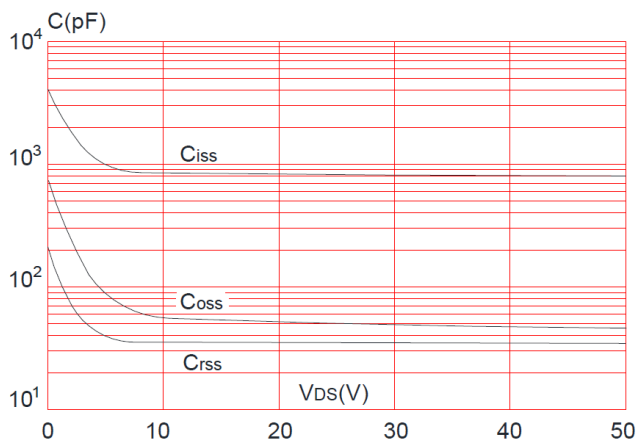
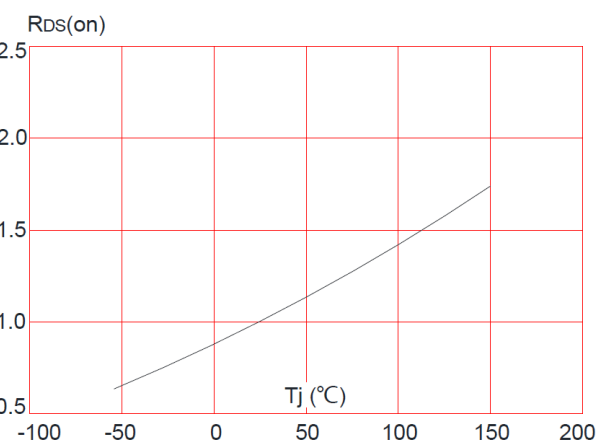
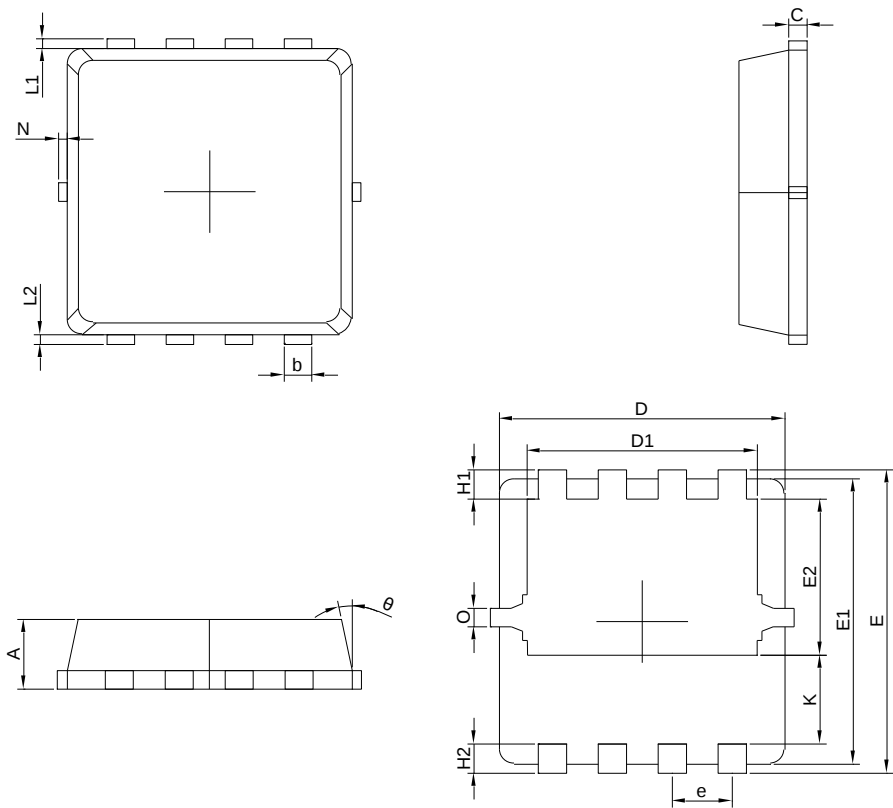


Figure 6: Normalized on Resistance vs. Junction Temperature



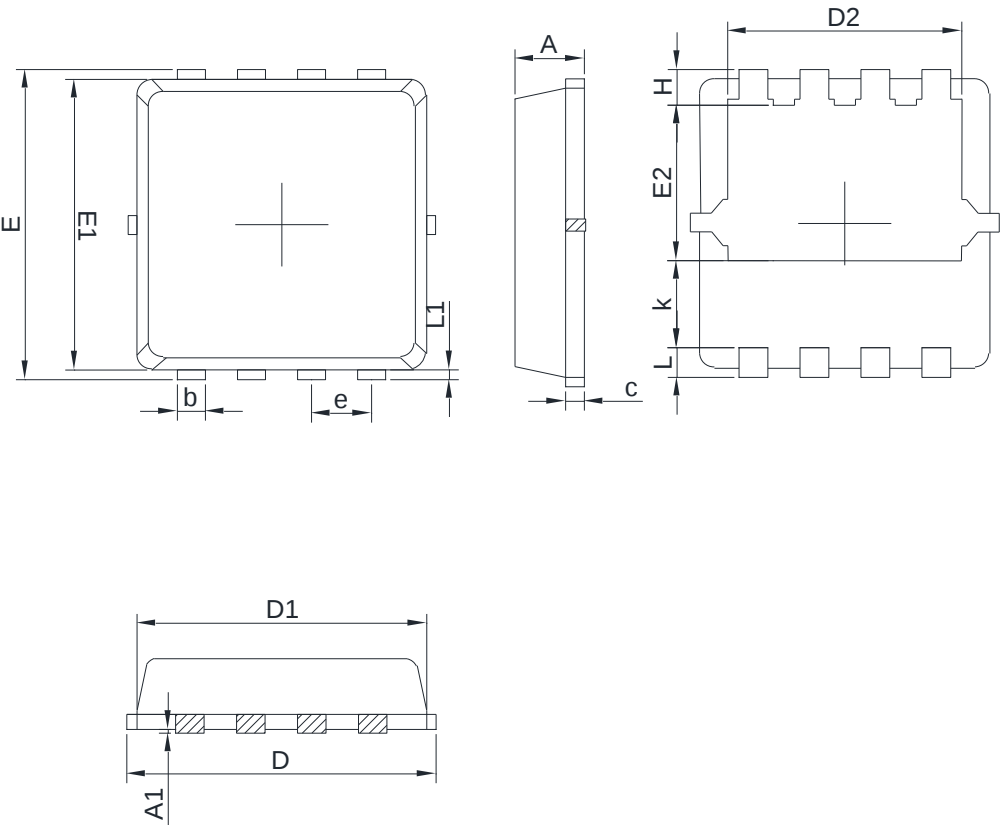
8. Dimension (PDFN3*3-8L)

POD A(J)



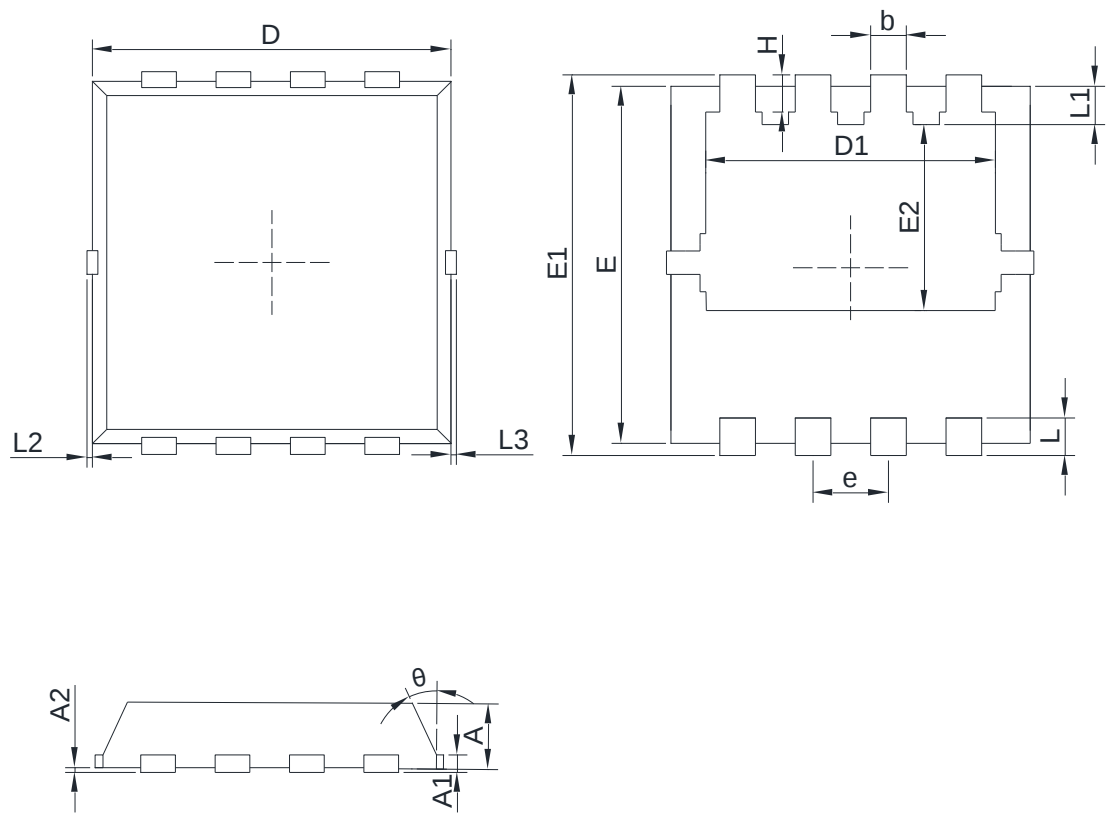
Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.65	0.75	0.85	e	0.65 BSC.		
b	0.25	0.30	0.35	H1	0.21	0.31	0.41
C	0.15	0.20	0.25	H2	0.30	0.40	0.50
D	3.00	3.10	3.20	K	0.78	0.88	0.98
D1	2.40	2.50	2.60	L1/L2	0.10 REF.		
E	3.20	3.30	3.40	θ	11°	12°	13°
E1	3.00	3.10	3.20	N	0	-	0.15
E2	1.60	1.70	1.80	O	0.2 REF.		

POD B(Q)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	Min.	NOM.	Max.		Min.	NOM.	Max.
A	0.65	0.75	0.85	H	0.385	0.485	0.585
A1			0.05	k	0.80		
b	0.20	0.30	0.40	L	0.30	0.40	0.50
c	0.10	0.15	0.25	e	0.65BCS		
D	3.05	3.20	3.35	L1	0.025	0.125	0.225
D1	3.05	3.15	3.25	D2	2.30	2.45	2.60
E	3.25	3.35	3.45	E2	1.36	1.51	1.66
E1	3.00	3.10	3.20				

POD C(X)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER							
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	0.700	0.800	0.900	L	0.300	0.400	0.500
A1	0.152 REF			L1	0.180	0.330	0.480
A2	0~0.05			L2	0~0.100		
D	3.000	3.100	3.200	L3	0~0.100		
D1	2.300	2.450	2.600	H	0.315	0.415	0.515
E	2.900	3.000	3.100	b	0.200	0.300	0.400
E1	3.150	3.300	3.450	e	0.550	0.650	0.750
E2	1.320	1.520	1.720	θ	8°	10°	12°

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